

IN THE SPECIFICATION:

Please amend the paragraph beginning on page 11, line 15 as follows:

A disc-like table 18 made of a non-conductive material such as alumina is provided in the process chamber 4. The table 18 includes a leg portion 20 having a hollow cylindrical shape. The leg portion 20 extends downward from the center of the bottom of the table 18. The bottom end of the leg portion 20 is connected to the bottom 6 of the process chamber 4 via a bellows 160 and a seal member such as an O-ring (both not shown in the figure). The bellows 160 and the O-ring are provided to allow the vertical movement of the table 18 while the interior of the leg portion 20 is hermetically separated from the space inside the process chamber 4.

Please amend the paragraph beginning on page 11, line 27 as follows:

The table 18 is mounted to an upper end of ~~a shaft 162~~ the leg portion 20 which is movable up and down by a vertical moving mechanism (not shown in the figure). A distance between the table 18 and a showerhead 50 provided above the table 18 can be varied by the vertical movement of the table 18. It should be noted that the showerhead 50 may be vertically moved instead of the table 18.

Please amend the paragraph beginning on page 15, line 3 as follows:

Additionally, the inner oxidation gas head space 58A is connected to a first oxidation gas supply passage 74 via a gas introduction port 72, and the outer oxidation gas head space 58B is connected to a second oxidation gas supply passage ~~[[74]]~~ 78 via a gas introduction port ~~[[72]]~~ 76. A third and fourth open/close valves 67C and 67D are provided in the middle of the first and second oxidant gas supply passages 74 and 78, respectively.

Please amend the paragraph beginning on page 15, line 17 as follows:

Each of the injection openings 52 for injecting the raw material gas communicates with either the inner raw material gas head spaces 56A or the outer raw material gas head spaces 56B. Each of the injection openings for injecting the oxidant gas communicates with either the inner oxidant gas head space 58A or the outer oxidant gas head space 58B. Specifically, as shown in FIG. 2, the gas injection surface 57 is divided into two zones, one is an inner zone 84 and the other is an outer zone 86. ~~the~~ The inner zone 84 is located in the center of the gas injection surface 57. The outer zone 86 has an annular shape so as to ~~surrounds~~ surround the inner zone 84. In FIG. 2, the boundary between the inner zone 84 and the outer zone is indicated by a single dashed chain line 88.

Please amend the paragraph beginning on page 21, line 5 as follows:

Additionally, in the second process performed under the relatively low vacuum, a distance between the wafer W and the showerhead 50 must be smaller than that in the first process performed under the high vacuum environment. Specifically, the distance between the wafer W and the showerhead 50 is in the range from 5 mm to 30 mm. In the low vacuum environment, the raw material gas and the oxidant gas reach the wafer W according to viscous flow. Accordingly, the efficiency of usage of the raw material gas and the oxidant gas decreases as the distance between the showerhead 50 and wafer W increases. This means that the efficiency of usage of the raw material gas and the oxidant gas increases as the distance between the showerhead 50 and wafer W decreases, which increases a film deposition rate.